

#### **Thesis**

Submitted for the Degree of Doctor of Teacher's Preparation in Science (Physics).

#### $\mathbf{B}\mathbf{v}$

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2016

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# Title: Study the physical properties of ZnIn<sub>2</sub>Se<sub>4</sub> for photovoltaic applications

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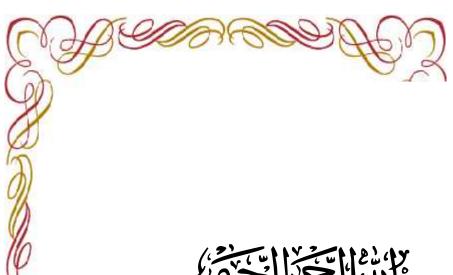
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بناتالجائي

" سبحانك لا علم لنا إلا ما علمتنا انك أنت العليم الحكيم"

صدوالك للعظهيم

# **ACKNOWLEDGMENT**

Before all and above all, many thanks to Allah, the most gracious, the most merciful.

The author wishes indebted with his utmost thanks to *Prof. Dr. Mahmoud Mohammed El-Nahass* for continuous supervision, valuable suggestions, encouragement and fruitful advice through this work.

Deepest gratitude to *Dr. Attia Abd El-Motteleb Attia* for his advice, valuable help and encouragement during this study.

The author wishes to thank *Dr. Hend Ali Mohammed* for her valuable help, encouragement and fruitful advice throughout this work.

Thanks to *Dr. Gehan Farook Abdh* for her valuable help, encouragement and fruitful advice throughout this work.

Thanks are also due to *Dr. Ahmed Mahmoud Nawar*, Faculty of Science - Suez Canal University, for his kind assistance and continuous encouragement help.

My deep thanks to all the staff members and colleagues of the thin film and solid state laboratories, Faculty of Education, Ain Shams University.

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